



PRODUCT CHANGE NOTICE

1. TITLE IRHNM57110, Radiation Test (TID) Specification Change		2. DOCUMENT NUMBER FV5-C-18-0007
		3. DATE October 23, 2017
4. MANUFACTURER AND ADDRESS International Rectifier HiRel Products, Inc 205 Crawford Street Leominster, MA 01453		5. MANUFACTURER PART NUMBER See below for IR Part Numbers
		6. BASE PART NA
		7. NATIONAL STOCK NUMBER (NSN) NA
8. CAGE 69210	9. EFFECTIVE DATE October 23, 2017	10. GOVERNMENT NUMBER NA
11. POINT OF CONTACT Manufacturer's Representative or Account Specialist (978) 534-5776		12. DRAWING NUMBER NA
		13. SPECIFICATION NUMBER MIL-PRF-19500/743
14. PRODUCT CHANGE This GIDEP PCN is to announce a change in the Radiation Test (TID) specifications for the following part number. Datasheet change to match MIL-PRF-19500/743 TID test limits. IRHNM57110 [JANSR2N7503U8] 100V, Single N-Channel TID Hardened MOSFET in a SMD-0.2 package  RADIATION CHARACTERISTICS CHANGE: Table 1 Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation RDS(on) Static Drain-to-Source On-State Resistance (TO-3) -For Up to 300K Rads(Si), change from 0.22 ohm to 0.226 ohm maximum Change Column Heading from Up to 300k Rads(Si) to Up to 500K Rads(Si) Add new column for 1000K Rads(Si) rating and associated parameter limits (as shown below) BVDSS Drain-to-Source Breakdown Voltage, min limit = 100V VGS(th) Gate Threshold Voltage, min limit = 1.5V, max limit = 4.0V IGSS Gate-to-Source Leakage Forward, max limit = 100nA IGSS Gate-to-Source Leakage Reverse, max limit = -100nA IDSS Zero Gate Voltage Drain Current, max limit = 10uA RDS(on) Static Drain-to-Source, On-State Resistance (TO-3), max limit = 0.246 ohm RDS(on) Static Drain-to-Source, On-state Resistance (SMD-0.2), max limit = 0.246 ohm VSD Diode Forward Voltage. max limit = 1.2V Reference Datasheet PD-97192		
16. APPROVING GOVERNMENT ACTIVITY		
17. GIDEP REPRESENTATIVE Paul Hebert	18. SIGNATURE 	19. DATE October 23, 2017